

FORM PTO-1449 SAMUELS, GAUTHIER & SONS LLP
(Rev. 5/92) 225 Franklin Street Boston, MA 02110
Telephone: (617) 426-9180

ATTORNEY DOCKET # 596

SERIAL NO. 09/884,517

Fitzgerald et al.
APPLICANT

Unknown
GROUP

IDS #4

6/19/01
FILING DATE

Unknown
EXAMINER

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

AUG 01 2001

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KP	AA	4,710,788	12/1/87	Dämbkes et al.			12/1/86
KP	AB	5,241,197	8/31/93	Murakami et al.			9/13/91
KP	AC	5,534,713	6/9/96	Ismail et al.			5/20/94
KP	AD	5,777,347	7/7/98	Bartelink			6/18/97
KP	AE	5,808,344	9/15/98	Ismail et al.			2/4/97
KP	AF	5,906,951	5/25/99	Chu et al.			4/30/97
KP	AG	6,013,134	1/11/00	Chu et al.			2/18/98
KP	AH	6,059,895	5/9/00	Chu et al.			5/13/99
KP	AI	6,111,367	8/29/00	Fischer et al.			5/4/98
KP	AJ	6,107,653	8/22/00	Fitzgerald			6/23/98

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AK						
	AL						
	AM						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
KP	AN	J. Welser, "The Application of Strained Silicon/Relaxed Silicon Germanium Heterostructures to Metal-Oxide-Semiconductor Field-Effect Transistors," PhD Thesis, Stanford University, 1995, pgs: 1-205
KP	AO	"Technology for SiGe Heterostructure-Based CMOS Devices" by Mark Albert Armstrong; PhD Thesis, Massachusetts Institute of Technology, 1999; pgs: 1-154
KP	AP	"Application of Silicon-Based Heterostructures To Enhanced Mobility Metal-Oxide-Semiconductor Field-Effect Transistors" by Kern Rim; PhD Thesis, Stanford University, 1999; pgs: 1-184
KP	AQ	"Fabrication and Analysis of Deep Submicron Strained-Si N-MOSFET's"; Rim et al.; IEEE Transactions on Electron Devices, Vol. 47, No. 7, July 2000; pgs: 1406-1415
KP	AR	"Enhanced Hole Mobilities in Surface-channel Strained-Si p-MOSFET's"; Rim et al.; Solid State Electronics Laboratory, Stanford University, Stanford, CA 94305; pgs: 20.3.1-20.3.4
KP	AS	"High-Mobility Strained-Si PMOSFET's"; Nayak et al.; IEEE Transactions On Electron Devices, Vol. 43, No. 10, October 1996; pgs: 1709-1716
KP	AT	"Electron and Hole Mobility Enhancement in Strained-Si MOSFET's on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology"; by Mizuno et al.; IEEE Electron Device Letters, Vol. 21, No. 5, May 2000; pgs: 230-232

EXAMINER

DATE CONSIDERED

04-21-02

EXAMINER:

Initial if citation considered, whether relevant citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

IDS # 6 1 of 2

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) FIS920010259		Application Number Unassigned	
				Applicant(s) Jack A. Mandelman, et al.			
				Filing Date Herewith		Group Art Unit Unassigned	

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KD		6,266,278	07/24/01	Harari, et al.			
KP		6,249,022	06/19/01	Lin, et al.			
KD		6,204,529	03/20/01	Lung, et al.			
KP		6,143,636	11/07/00	Forbes, et al.			
KD		6,130,453	10/10/00	Mei, et al.			
KD		6,058,044	05/02/00	Sugiura, et al.			
KP		5,786,612	07/28/98	Otani, et al.			
KP		5,739,567	04/14/98	Wong			
KP		5,617,351	04/01/97	Bertin, et al.			
KP		5,596,527	01/12/97	Tomioka, et al.			
KD		5,291,439	03/01/94	Kauffmann, et al.			

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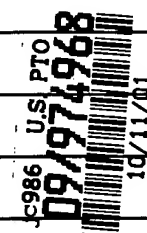
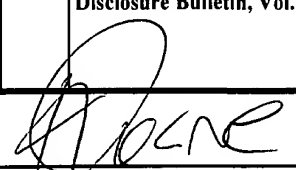
FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>	
	English language Abstract of Japanese Patent No. JP 7106446, issued April 21, 1995
	English language Abstract of Japanese Patent No. JP 4307974, issued October 30, 1992

EXAMINER	DATE CONSIDERED 08-05-2002
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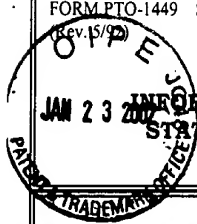
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

IDS # 6 2 of 2

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) FIS920010259US1 (898)		Application Number Unassigned		
				Applicant(s) Jack A. Mandelman, et al.				
				Filing Date Herewith		Group Art Unit Unassigned		
U.S. PATENT DOCUMENTS								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
RP		4,990,979	02/05/91	Otto				
FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>								
		English language Abstract of Japanese Patent No. JP 11233744, issued August 27, 1999						
		"2 BIT/CELL EEPROM CELL USING BAND-TO-BAND TUNNELING FOR DATA READ-OUT", IBM Technical Disclosure Bulletin, Vol. 35, No. 4B, pp. 136-140, September 1992						
EXAMINER				DATE CONSIDERED				
				08-05-2002				
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

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FORM PTO-1449 (Rev. 15/92) SAMUELS, GAUTHIER & STEVENS LLP 225 Franklin Street, Boston, MA 02110 Telephone: (617) 426-9180	ATTORNEY DOCKET NO. 5994A Fitzgerald et al. APPLICANT 6/19/01 FILING DATE	SERIAL NO. 09/884,517 Unknown GROUP Unknown EXAMINER
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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MBD	AA	6,111,267	8/29/00	Fischer et al.			5/4/98
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						

RECEIVED
ED-8
TC 2806
MAIL ROOM

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AK						
	AL						
	AM						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	AN	
	AO	
	AP	
	AQ	
	AR	
	AS	
	AT	

EXAMINER: <i>[Signature]</i>	DATE CONSIDERED: 11/18/2002
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SHEET 1 OF 1

FORM PTO - 1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT				ATTORNEY DOCKET NO.: ASC-043 APPLICANT(S): Eugene A. Fitzgerald et al. SERIAL NO.: 09/884,517 FILING DATE: June 19, 2001 GROUP: 2822					
U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
KBP		5,998,807	12/7/99	Lustig et al.	257	66	9/9/97		
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
EXAMINER	[Signature]				DATE CONSIDERED 11/18/02				

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